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Quad Operational Amplifier



ADE-204-045 (Z) Rev. 0 Dec. 2000

Description

The HA17902 is an internal phase compensation quad operational amplifier that operates on a single-voltage power supply and is appropriate for use in a wide range of general-purpose control equipment.

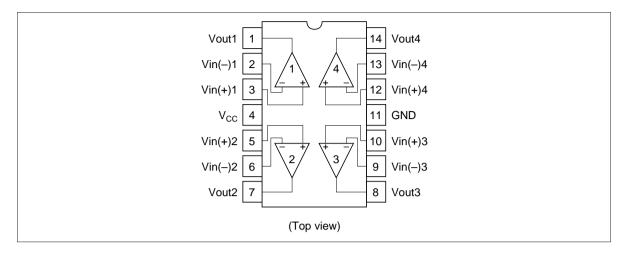
Features

- · Wide usable power-supply voltage range and single-voltage supply operation
- · Internal phase compensation
- Wide common-mode voltage range and operation for inputs close to the 0 level

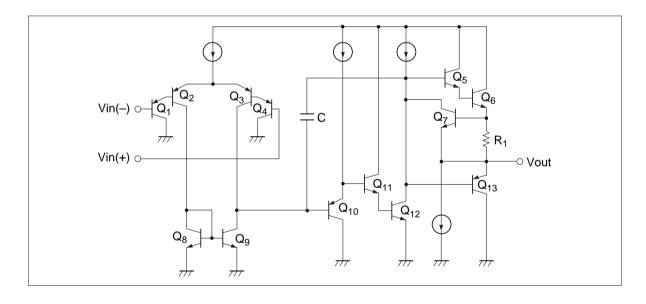
Ordering Information

Type No.	Application	Package		
HA17902PJ	Car use	DP-14		
HA17902FPJ		FP-14DA		
HA17902FPK		FP-14DA		
HA17902P	Industrial use	DP-14		
HA17902FP		FP-14DA		
HA17902	Commercial use	DP-14		

Pin Arrangement



Circuit Structure (1/4)



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	HA17902/ P	HA17902 PJ	HA17902 FP	HA17902 FPJ	HA17902 FPK	Unit
Power supply voltage	V _{cc}	28	28	28	28	28	V
Sink current	lo sink	50	50	50	50	25	mA
Allowable power dissipation	P _T	625* ¹	625*1	625*2	625*2	625*2	mW
Common-mode input voltage	V_{CM}	–0.3 to V _{cc}	–0.3 to V _{cc}	–0.3 to V _{cc}	–0.3 to V _{cc}	–0.3 to V _{cc}	V
Differential-mode input voltage	Vin(diff)	±V _{cc}	±V _{cc}	±V _{cc}	±V _{cc}	±V _{cc}	V
Operating temperature	Topr	-20 to +75	-40 to +85	−20 to +75	-40 to +85	-40 to +125	°C
Storage temperature	Tstg	-55 to +125	-55 to +125	-55 to +125	-55 to +125	-55 to +150	°C

Notes: 1. These are the allowable values up to $Ta = 50^{\circ}C$. Derate by $8.3 \text{mW}/^{\circ}C$ above that temperature.

^{2.} See notes on SOP Package Usage in Reliability section.

Electrical Characteristics 1 ($V_{CC} = +15V$, $Ta = 25^{\circ}C$)

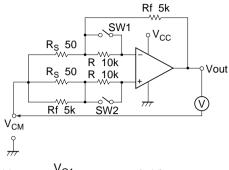
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Input offset voltage	V _{IO}	_	3	8	mV	$V_{CM} = 7.5V$, $R_S = 50\Omega$, $Rf = 5k\Omega$
Input offset current	I _{IO}	_	5	50	nA	$I_{10} = I_1^ I_1^+ , V_{CM} = 7.5V$
Input bias current	I _{IB}	_	30	500	nA	V _{CM} = 7.5V
Power-supply rejection ratio	PSRR	_	93	_	dB	$f = 100Hz$, $R_S = 1k\Omega$, $Rf = 100k\Omega$
Voltage gain	A _{VD}	75	90	_	dB	$R_S = 1k\Omega$, $Rf = 100k\Omega$, $RL = \infty$
Common-mode rejection ratio	CMR	_	80	_	dB	$R_s = 50\Omega$, $Rf = 5k\Omega$
Common-mode input voltage range	V_{CM}	-0.3	-	13.5	V	$R_s = 1k\Omega$, $Rf = 100k\Omega$, $f = 100Hz$
Maximum output voltage amplitude	V_{OP-P}	_	13.6	-	V	$\begin{split} &f=100 Hz, \ R_{_{S}}=1 k\Omega, \ Rf=100 k\Omega, \\ &R_{_{L}}=20 k\Omega \end{split}$
Output voltage	V_{OH1}	13.2	13.6	_	V	$I_{OH} = -1 \text{mA}$
	V_{OH2}	12	13.3	_	V	$I_{OH} = -10 \text{mA}$
	V_{OL1}	_	8.0	1	V	I _{OL} = 1mA
	V_{OL2}	_	1.1	1.8	V	I _{OL} = 10mA
Output source current	lo source	15	_	_	mA	V _{OH} = 10V
Output sink current	lo sink	3	9	_	mA	$V_{OL} = 1V$
Supply current	I _{cc}	_	8.0	2	mA	Vin = GND, $R_L = \infty$
Slew rate	SR		0.19		V/µs	$f = 1.5kHz, V_{CM} = 7.5V, R_{L} = \infty$
Channel separation	CS	_	120	_	dB	f = 1kHz

Electrical Characteristics 2 ($V_{CC} = +\ 15V,\ Ta = -\ 40\ to\ 125^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Input offset voltage	V _{IO}	_	_	8	mV	$V_{CM} = 7.5V$, $R_S = 50\Omega$, $Rf = 5k\Omega$
Input offset current	I _{IO}	_	_	200	nA	$V_{CM} = 7.5V$, $I_{IO} = I_I^ I_I^+ $
Input bias current	I _{IB}	_	_	500	nA	V _{CM} = 7.5V
Common-mode input voltage range	V _{CM}	0	_	13.0	V	$R_s = 1k\Omega$, $Rf = 100k\Omega$, $f = 100Hz$
Output voltage	V _{OH}	13.0	_	_	V	$I_{OH} = -1 \text{mA}$
	V _{OL}	_	_	1.3	V	I _{OL} = 1mA
Supply current	I _{cc}	_	_	4	mA	$Vin = GND, R_L = \infty$

Test Circuits

1. Input offset voltage (V_{IO}), input offset current (I_{IO}), and Input bias current (I_{IB}) test circuit



SW1	SW2	v_o	
On	On	V _{O1}	1
Off	Off	V _{O2}	$V_{CM} = \frac{1}{2} V_{CC}$
On	Off	V _{O3}	_
Off	On	V_{O4}	

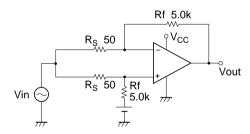
$$V_{IO} = \frac{V_{O1}}{1 + Rf/R_S}$$
 (mV)

$$I_{IO} = \frac{V_{O2} - V_{O1}}{R(1 + Rf / R_S)}$$
 (nA)

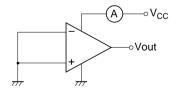
$$I_{IB} = \frac{|V_{O4} - V_{O3}|}{2 \cdot R(1 + Rf/R_S)}$$
 (nA)

2. Common-mode rejection ratio (CMR) test circuit

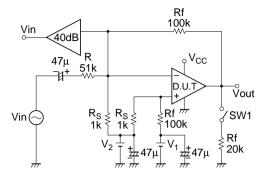
$$CMR = 20 log \frac{V_{IN} \cdot Rf}{V_O \cdot R_S} \quad (dB)$$



3. Supply current (I_{CC}) test circuit



4. Voltage gain (A_{VD}) , slew rate (SR), common-mode input voltage range (V_{CM}) , and maximum output voltage amplitude (V_{OP-P}) test circuit.



(1)
$$A_{VD}$$
: $R_S = 1k\Omega$, $Rf = 100k\Omega$, $R_L = \infty$, $V_1 = V_2 = 1/2 \ V_{CC}$
$$A_{VD} = 20 \ log \ \frac{V_O}{V_{IN}} + 40 \qquad \text{(dB)}$$

(2) SR: f = 1.5 kHz, $R_L = \infty$, $V_1 = V_2 = 1/2 \text{ V}_{CC}$

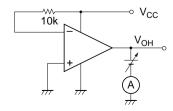
$$SR = \frac{V}{T} [V/\mu s]$$

- (3) V_{CM} : $R_{\text{S}} = 1 \text{k}\Omega$, $Rf = 100 \text{k}\Omega$, f = 100 Hz, $V_{1} = 1/2$ V_{CC} , $R_{L} = \infty$, and the value of V_{2} just slightly prior to the point where the output waveform changes.
- (4) V_{OP-P} : $R_S = 1k\Omega$, $Rf = 100k\Omega$, R_L : $20k\Omega$, f = 100Hz, $V_{OP-P} = V_{OH} \leftrightarrow V_{OL} [V_{P-P}]$
- 5. Output source current (Iosource) test circuit Io source: $V_{OH} = 10V$

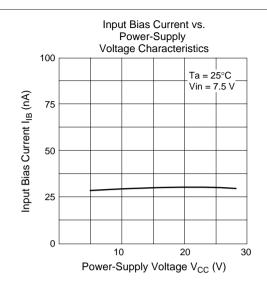
V_{OH}

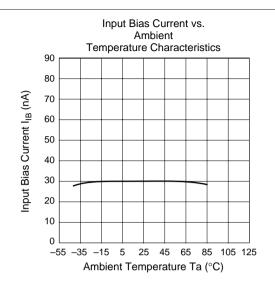
6. Output sink current (Iosink) test circuit

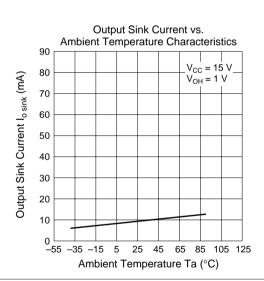
Io sink: $V_{OL} = 1V$

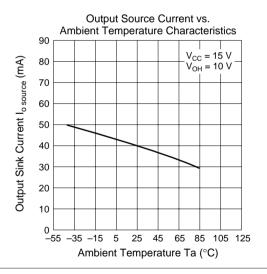


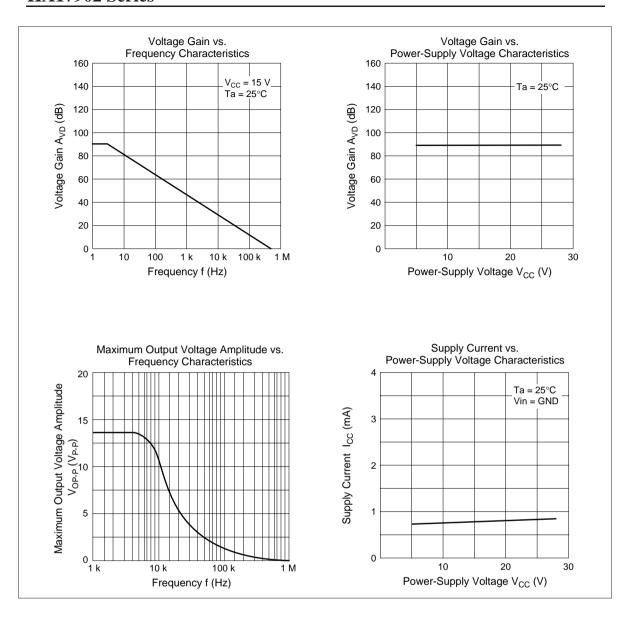
Characteristics Curve

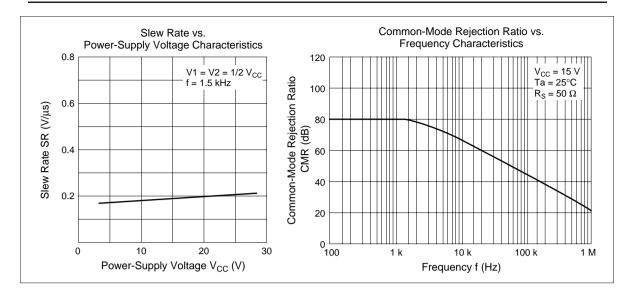


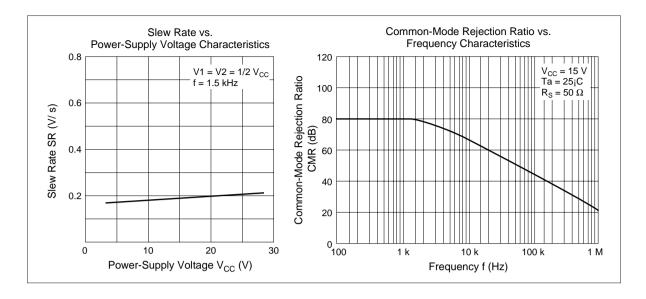












HA17902 Application Examples

The HA17902 is a quad operational amplifier, and consists of four operational amplifier circuits and one bias current circuit. It features single-voltage power supply operation, internal phase compensation, a wide zero-cross bandwidth, a low input bias current, and a high open-loop gain. Thus the HA17902 can be used in a wide range of applications. This section describes several applications using the HA17902.

1. Noninverting Amplifier

Figure 1 shows the circuit diagram for a noninverting amplifier. The voltage gain of this amplifier is given by the following formula.

$$\frac{Vout}{Vin} = 1 + \frac{R2}{R1}$$

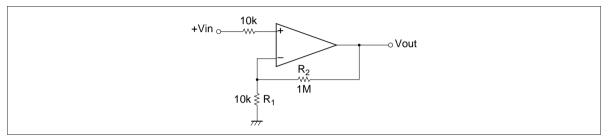


Figure 1 Noninverting Amplifier

2. Summing Amplifier

Since the circuit shown in figure 2 applies $+V_1$ and $+V_2$ to the noninverting input and $+V_3$ and $+V_4$ to the inverting input, the total output will be Vout = $V_1 + V_2 - V_3 - V_4$.

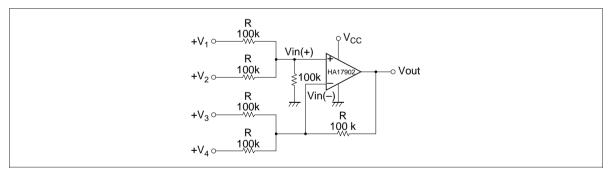


Figure 2 Summing Amplifier

3. High Input Impedance DC Differential Amplifier

The circuit shown in figure 3 is a high input impedance DC differential amplifier. This circuit's common-mode rejection ratio (CMR) depends on the matching between the R_1/R_2 and R_4/R_3 resistance ratios. This amplifier's output is given by the following formula.

Vout =
$$\left(1 + \frac{R_4}{R_3}\right) (V_2 - V_1)$$

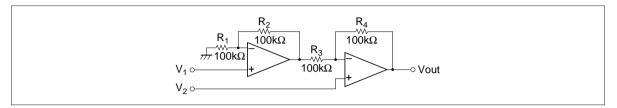


Figure 3 High Input Impedance DC Differential Amplifier

4. Voltage Controlled Oscillator

Figure 4 shows an oscillator circuit in which the amplifier A_1 is an integrator, the amplifier A_2 is a comparator, and transistor Q_1 operates as a switch that controls the oscillator frequency. If the output Vout1 is at the low level, this will cut off transistor Q1 and cause the A_1 inverting input to go to a higher potential than the noninverting input. Therefore, A_1 will integrate this negative input state and its output level will decrease. When the A_1 integrator output becomes lower than the A_2 comparator noninverting input level ($V_{CC}/2$) the comparator output goes high. This turns on transistor Q_1 causing the integrator to integrate a positive input state and for its output to increase. This operation generates a square wave on Vout1 and a triangular wave on Vout2.

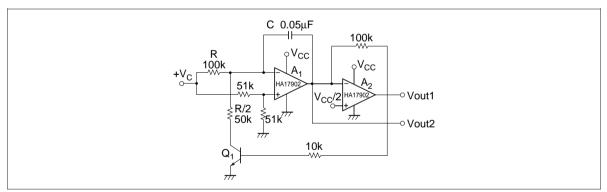
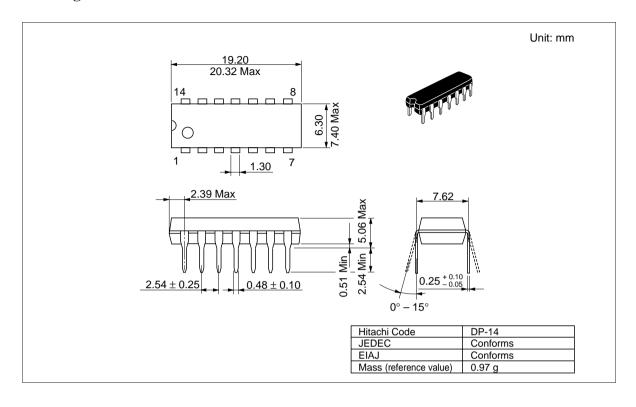
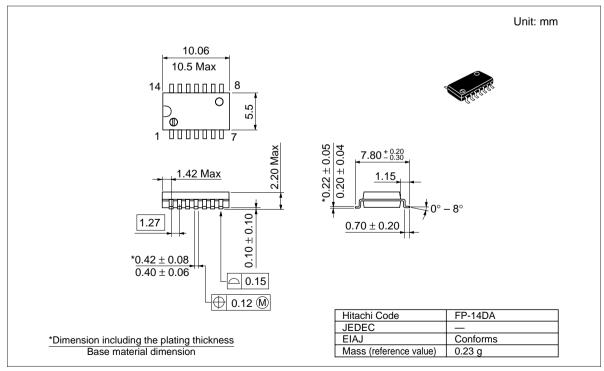


Figure 4 Voltage Controlled Oscillator

Package Dimensions





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